

L Number	Hits	Search Text	DB	Time stamp
-	20	(byoung adj2 ho near3 lim).in.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/03/08 11:17
-	528	(349/187).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/03/08 11:17
-	124	(349/192).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/03/08 11:17
-	33	((((349/187).CCLS.) ((349/192).CCLS.)) and etch\$3 same substrate ) and wet and dry	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/03/08 11:28
-	157	((349/187).CCLS.) and etch\$3 same substrate	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/03/09 19:40
-	132	((349/187).CCLS.) and substrate same (thin thinner) and etch\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/03/08 17:14
-	1	((216/80).CCLS.) and dry adj2 etch\$3 same (clean cleaning)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/03/08 17:29
-	8	((216/80).CCLS.) and dry adj2 etch\$3 same substrate and (clean cleaning)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/03/08 17:30
-	43	((216/23).CCLS.) and dry adj2 etch\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/03/09 09:35
-	190	(216/80).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/03/09 10:54
-	47	((216/80).CCLS.) and ((dry plasma) adj2 etch\$3 RIE CDE half adj ash) and (clean cleaning impurities planarized planarization)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/03/09 10:57
-	36	((216/80).CCLS.) and ((dry plasma) adj2 etch\$3 RIE CDE half adj ash) same substrate and (clean cleaning impurities planarized planarization)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/03/09 11:22
-	269	(349/97).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/03/09 11:22
-	4	((349/97).CCLS.) and ((dry plasma) adj2 etch\$3 RIE CDE half adj ash)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/03/09 11:26
-	1345	(349/158).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/03/09 11:26
-	61	(349/160).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/03/09 11:30
-	28	((349/160).CCLS.) and etch\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/03/09 11:36

-	185	((349/158).CCLS.) and etch\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/03/09 11:46
-	38	((349/158).CCLS.) and ((dry plasma) adj2 etch\$3 RIE CDE half adj ash)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/03/09 11:37
-	145	((349/158).CCLS.) and etch\$3.) not (((349/158).CCLS.) and ((dry plasma) adj2 etch\$3 RIE CDE half adj ash)) ((349/160).CCLS.) and etch\$3 ) ((216/23).CCLS.)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/03/09 19:40
-	180	((349/187).CCLS.) ((349/192).CCLS.)) and etch\$3 same substrate	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/03/09 11:48
-	28	((349/192).CCLS.) and etch\$3 same substrate	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/03/09 11:48
-	288	(438/704).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/03/09 13:23
-	8	((438/704).CCLS.) and (LCD liquid adj crystal)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/03/09 13:24
-	99	((438/704).CCLS.) and (glass transparent adj2 substrate).	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/03/09 13:34
-	57	((216/23).CCLS.) and ((dry plasma) adj2 etch\$3 RIE CDE half adj ash)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/03/09 15:23
-	8	5249422.URPN.	USPAT	2003/03/09 16:33
-	139	(216/23).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/03/09 17:06
-	38	((216/23).CCLS.) and etch\$3 same substrate and wet and (dry RIE CDE half adj ash plasma)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/03/09 17:27
-	6	5851411.URPN.	USPAT	2003/03/09 17:21
-	72	349/\$.ccls. and etch\$3 same substrate and ((dry plasma)adj2 etch\$3 RIE CDE half adj ash) and (planarize planarization planarized cleaning) and (process method).ti.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/03/09 17:32

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